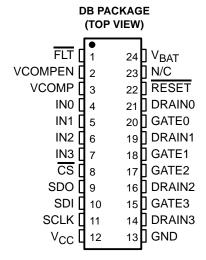
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- 4-Channel Serial-In Parallel-In Low-Side **Pre-FET Driver**
- **Devices Are Cascadable**
- Internal 55-V Inductive Load Clamp and V<sub>GS</sub> Protection Clamp for External Power
- Independent Shorted-Load/Short-to-**Battery Fault Detection on All Drain Terminals**
- **Independent OFF-State Open-Load Fault** Sense
- **Over-Battery-Voltage Lockout Protection** and Fault Reporting
- **Under-Battery Voltage Lockout Protection** for the TPIC44L01 and TPIC44L02

## description

The TPIC44L01, TPIC44L02, and TPIC44L03 are low-side predrivers that provide serial and parallel input interfaces to control four external FET power switches such as offered in the TI TPIC family of power arrays. These devices are designed primarily for low-frequency switching, inductive load applications such as solenoids and relays. Fault status for each channel is available in a serial-data format. Each driver channel has independent off-state open-load detection and on-state shorted-load/short-to-battery detection. Battery overvoltage and undervoltage detection and shutdown is provided on the TPIC44L01/L02. On the TPIC44L03 driver, only over-battery voltage shutdown is provided. Each channel also provides inductive-voltage-transient protection for the external FET.

- **Asynchronous Open-Drain Fault Flag**
- **Device Output Can Be Wire-ORed With Multiple Devices**
- **Fault Status Returned Through Serial Output Terminal**
- Internal Global Power-On Reset of Device and External RESET Terminal
- **High-Impedance CMOS-Compatible Inputs** With Hysteresis
- TPIC44L01 and TPIC44L03 Disables the Gate Output When a Shorted-Load Fault Occurs
- TPIC44L02 Transitions the Gate Output to a Low-Duty Cycle PWM Mode When a Shorted-Load Fault Occurs



These devices provide control of output channels through a serial input interface or a parallel input interface. A command to enable the output from either interface enables the respective channels gate output to the external FET. The serial interface is recommended when the number of signals between the control device and the predriver must be minimized and the speed of operation is not critical. In applications where the predriver must respond very quickly or asynchronously, the parallel input interface is recommended.

For serial operation, the control device must transition  $\overline{CS}$  from high to low to activate the serial input interface. When this occurs, SDO is enabled, fault data is latched into the serial interface, and the fault flag is refreshed.



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# description (continued)

Data is clocked into the serial registers on low-to-high transitions of SCLK through SDI. Each string of data must consist of at least four bits of data. In applications where multiple devices are cascaded together, the string of data must consist of four bits for each device. A high data bit turns the respective output channel on and a low data bit turns it off. Fault data for the device is clocked out of SDO as serial input data is clocked into the device. Fault data consists of fault flags for shorted-load and open-load flags (bits 0–3) for each of the four output channels. A high bit in the fault data indicates a fault and a low bit indicates that no fault is present for that channel. Fault register bits are set or cleared asynchronously to reflect the current state of the hardware. A fault must be present when  $\overline{CS}$  is transitioned from high to low to be captured and reported in the serial fault data. New faults cannot be captured in the serial register when  $\overline{CS}$  is low.  $\overline{CS}$  must be transitioned high after all of the serial data has been clocked into the device. A low-to-high transition of  $\overline{CS}$  transfers the last four bits of serial data to the output buffer puts SDO in a high-impedance state and clears and reenables the fault register. The TPIC44L01/L02/L03 was designed to allow the serial input interfaces of multiple devices to be cascaded together to simplify the serial interface to the controller. Serial input data flows through the device and is transferred out SDO following the fault data in cascaded configurations.

For parallel operation, data is transferred directly from the parallel input interface IN0-IN3 to the respective GATE(0-3) output asynchronously. SCLK or  $\overline{\text{CS}}$  is not required for parallel control. A 1 on the parallel input turns the respective channel on, where a 0 turns it off. Note that either the serial input interface or the parallel input interface can enable a channel. Under parallel operation, fault data must still be collected through the serial data interface.

The predrivers monitor the drain voltage for each channel to detect shorted-load or open-load fault conditions in the the on and off states respectively. These devices offer the option of using an internally generated fault-reference voltage or an externally supplied fault-reference voltage through VCOMP for fault detection. The internal fault reference is selected by connecting VCOMPEN to GND and the external reference is selected by connecting VCOMPEN to VCC. The drain voltage is compared to the fault reference when the channel is turned on to detect shorted-load conditions and when the channel is off to detect open-load conditions. When a shorted fault occurs using the TPIC44L01 or the TPIC44L03, the channel is turned off and a fault flag is sent to the control device as well as to the serial fault register bits. If a fault occurs while using the TPIC44L02, the channel transitions into a low-duty cycle, pulse-width-modulated (PWM) signal as long as the fault is present. Shorted-load fault conditions must be present for at least the shorted-load deglitch time,  $t_{\rm (STBDG)}$ , to be flagged as a fault. A fault flag is sent to the control device as well as the serial fault register bits. More detail on fault detection operation is presented in the device operation section of this data sheet.

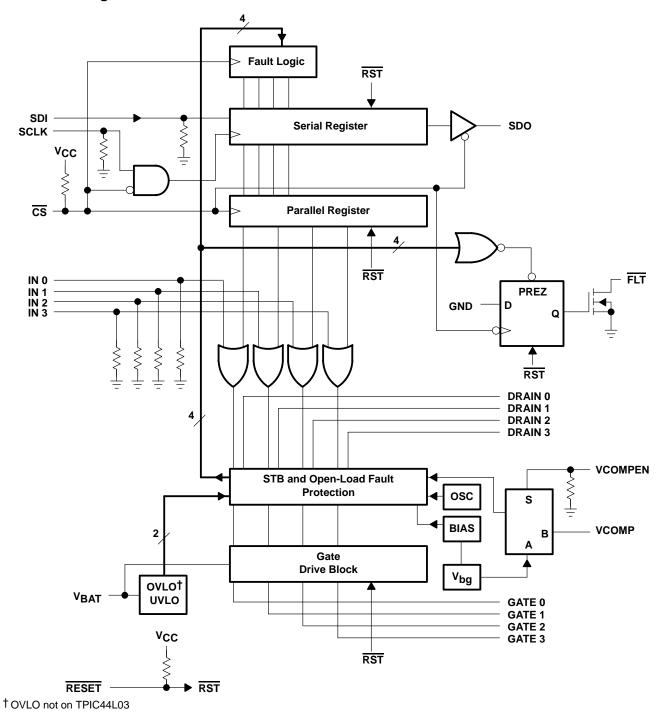
These devices provide protection from over-battery voltage and under-battery voltage conditions irrespective of the state of the output channels. When the battery voltage is greater than the overvoltage threshold or less than the undervoltage threshold, all channels are disabled and a fault flag is generated. Battery-voltage faults are not reported in the serial fault data. The outputs return to normal operation once the battery-voltage fault has been corrected. When an over-battery/under-battery voltage condition occurs, the device reports the battery fault, but disables fault reporting for open- and shorted-load conditions. Fault reporting for open- and shorted-load conditions are reenabled after the battery fault condition has been corrected.

These devices provide inductive transient protection on all channels. The drain voltage is clamped to protect the FET. The clamp voltage is defined by the sum of  $V_{CC}$  and turnon voltage of the external FET. The predriver also provides a gate-to-source voltage ( $V_{GS}$ ) clamp to protect the gate-source terminals of the power FET from exceeding their rated voltages. An external active low  $\overline{RESET}$  is provided to clear all registers and flags in the device. GATE(0–3) outputs are disabled after  $\overline{RESET}$  has been pulled low.

These devices provide pulldown resistors on all inputs except  $\overline{\text{CS}}$  and  $\overline{\text{RESET}}$ . A pullup resistor is used on  $\overline{\text{CS}}$  and  $\overline{\text{RESET}}$ .



# schematic diagram



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# **Terminal Functions**

TERMINAL			DESCRIPTION			
NAME	NO.	1/0				
<u>cs</u>	8	I	Chip select. A high-to-low transition on $\overline{CS}$ enables SDO, latches fault data into the serial interface, and refreshes $\overline{FLT}$ . When $\overline{CS}$ is high, the fault registers can change fault status. On the falling edge of $\overline{CS}$ , fault data is latched into the serial output register and transferred using SDO and SCLK. On a low-to-high transition of $\overline{CS}$ , serial data is latched in to the output control register.			
DRAIN0	21	I	FET drain inputs. DRAIN0 through DRAIN3 are used for both open-load and short-circuit fault detection at the			
DRAIN1	19		drain of the external FETs. They are also used for inductive transient protection.			
DRAIN2	16					
DRAIN3	14					
FLT	1	I	Fault flag. FLT is a logic level open-drain output that provides a real-time fault flag for shorted-load/open-load/over-battery voltage/under-battery voltage faults. The device can be ORed with FLT terminals on other devices for interrupt handling. FLT requires an external pullup resistor.			
GATE0	20	0	Gate drive output. GATE0 through GATE3 outputs are derived from the VBAT supply voltage. Internal clamps			
GATE1	18		prevent voltages on these nodes from exceeding the V <sub>GS</sub> rating on most FETs.			
GATE2	17					
GATE3	15					
GND	13	I	Ground and substrate			
IN0	4	I	Parallel gate driver. IN0 through IN3 are real-time controls for the gate predrive circuitry. They are CMOS			
IN1	5		compatible with hysteresis.			
IN2	6					
IN3	7					
RESET	22	I	Reset. A high-to-low transition of RESET clears all registers and flags. Gate outputs turn off and the FLT flag is cleared.			
SCLK	11	I	Serial clock. SCLK clocks the shift register. Serial data is clocked into SDI and serial fault data is clocked out of SDO on the falling edge of the serial clock.			
SDI	10	I	Serial data input. Output control data is clocked into the serial register through SDI. A 1 on SDI commands a particular gate output on and a 0 turns it off.			
SDO	9	0	Serial data output. SDO is a 3-state output that transfers fault data to the controlling device. It also passes serial input data to the next stage for cascaded operation. SDO is taken to a high-impedance state when $\overline{\text{CS}}$ is in a high state.			
V <sub>BAT</sub>	24	I	Battery supply voltage			
Vcc	12	I	Logic supply voltage			
VCOMPEN	2	I	Fault reference voltage select. VCOMPEN selects the internally generated fault reference voltage (0) or an external fault reference (1) to be used in the shorted- and open-load fault detection circuitry.			
VCOMP	3	I	Fault reference voltage. VCOMP provides an external fault reference voltage for the shorted-load and open-load fault detection circuitry.			



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# absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V <sub>CC</sub> (see Note 1)	0.3 V to 7 V
Battery supply voltage range, V <sub>BAT</sub>	0.3 V to 60 V
Input voltage range,V <sub>I</sub> (at any input)	0.3 V to 7 V
Output voltage range, V <sub>O</sub> (SDO and FLT)	0.3 V to 7 V
Drain-to-source voltage, V <sub>DS</sub>	0.3 V to 60 V
Output voltage, VO	0.3 V to 15 V
Operating case temperature range, T <sub>C</sub>	40°C to 125°C
Thermal resistance, junction to ambient, R <sub>0JA</sub>	135°C/W
Maximum junction temperature, T <sub>J</sub>	150°C
Storage temperature range, T <sub>stg</sub>	–40°C to 150°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: All voltage values are with respect to GND.

# recommended operating conditions

	MIN	NOM	MAX	UNIT
Logic supply voltage, V <sub>CC</sub>	4.5	5	5.5	V
Battery supply voltage, V <sub>BAT</sub>	8		24	V
High-level input voltage, VIH	0.85 V <sub>C</sub> C		VCC	V
Low-level input voltage, V <sub>IL</sub>	0		0.15 V <sub>CC</sub>	V
Setup time, SDI high before SCLK rising edge, t <sub>SU</sub> (see Figure 5)	10			ns
Hold time, SDI high after SCLK rising edge, th (see Figure 5)	10			ns
Case temperature, T <sub>C</sub>	-40		125	°C

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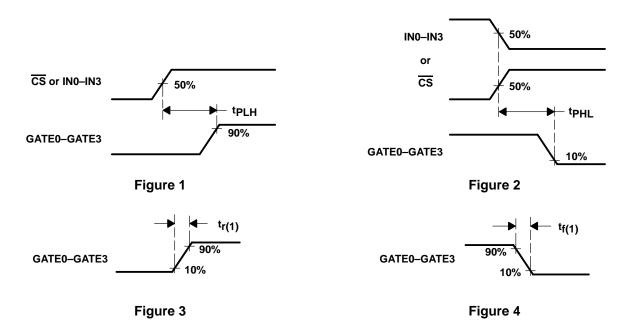
# electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

IBAT   Supply current, VBAT   All outputs off, VBAT = 12 V   300   500   700   μA     ICC   Supply current, VCC   All outputs off, VBAT = 12 V   1   2.6   4.2   mA     V(turnon)   Turnon voltage, logic operational, VCC   VBAT = 5.5 V, Check output functionality   2.6   3.5   4.4   V     V(vosd)   Over-battery-voltage shutdown   VBAT = 5.5 V, Check output functionality   32   34   36   V     V(vosd)   Under-battery-voltage shutdown   VPO   VBAT = 5.5 V, Check output functionality   32   34   36   V     V(vosd)   Under-battery-voltage shutdown   VPO   VRO		PARAMETER	TEST CONDITIONS		MIN	TYP	MAX	UNIT
V(turnon)   Turnon voltage, logic operational, VCC	I <sub>BAT</sub>	Supply current, VBAT	All outputs off,	V <sub>BAT</sub> = 12 V	300	500	700	μΑ
V(cusd)         Over-battery-voltage shutdown (PTICALLO2 only)         Check output functionality         2.6         3.5         4.7         V           V(ovsd)         Over-battery-voltage shutdown (PTICALLO1/LO2 only)         Cate disabled, See Figure 16         32         34         36         V           V(uvsd)         Under-battery-voltage reset hysteresis, (PTICALLO1/LO2 only)         acte disabled, See Figure 17         4.1         4.8         5.4         V           V <sub>O</sub> Under-battery-voltage reset hysteresis, (PTICALLO1/LO2 only)         acte disabled, See Figure 17         7         100         200         300         mV           V <sub>O</sub> Gate drive voltage         8 V < V <sub>BAT</sub> < 24 V, I <sub>O</sub> = 100 μA         7         13.5         V           V <sub>O</sub> Gate drive voltage         8 V < V <sub>BAT</sub> < 24 V, I <sub>O</sub> = 100 μA         7         13.5         V           V <sub>O</sub> Gate drive voltage         8 V < V <sub>BAT</sub> < 24 V, I <sub>O</sub> = 100 μA         7         13.5         V           V <sub>O</sub> Gate drive voltage         8 V < V <sub>BAT</sub> < 24 V, I <sub>O</sub> = 100 μA         7         13.5         V           V <sub>O</sub> Gate drive voltage         9 Gate drive voltage         9.5         1.2         2.5         mA           Io(L)         Maximum current output for drive terminals, pulldown	ICC	Supply current, V <sub>CC</sub>	All outputs off,	$V_{BAT} = 5.5 V$	1	2.6	4.2	mA
Vhys(ov)         Over-battery-voltage reset hysteresis         Gate disabled, Price of the p	V <sub>(turnon)</sub>			2.6	3.5	4.4	V	
Vhys(ov)         Over-battery-voltage reset hysteresis         O.5         1         1.5         V           V(uvsd)         Under-battery-voltage shutdown, (TPICA4L01/L02 only)         Bate disabled, See Figure 17         4.1         4.8         5.4         V           Vhys(uv)         Under-battery-voltage reset hysteresis, (TPICA4L01/L02 only)         BV < VBAT < 24 V, IQ = 100 μA	V <sub>(ovsd)</sub>	Over-battery-voltage shutdown	Cata diaablad	Coo Figure 16	32	34	36	V
Volume	V <sub>hys(ov)</sub>	Over-battery-voltage reset hysteresis	Gate disabled,	See Figure 16	0.5	1	1.5	V
Vhys(uv)         Under-battery-voltage reset hysteresis, (TPIC44L01/L02 only)         8 V < VBAT < 24 V, IQ = 100 μA         7         13.5         V           VG         Bate drive voltage         8 V < VBAT < 24 V, IQ = 100 μA	V <sub>(uvsd)</sub>	, ,			4.1	4.8	5.4	V
Vo   Sate drive voltage   5.5 \( \ \ \ V_{BAT} < 8 \ \ \ \ \ \ \ \ O_{O} = 100 \ \ \ \ A \  \  \ \ O_{O} \  \ O_{O} \	V <sub>hys(uv)</sub>		Gate disabled,	See Figure 17	100	200	300	mV
IO(H)   Maximum current output for drive terminals, pullup   VO = GND   O.5   1.2   2.5   mA     IO(L)   Maximum current output for drive terminals, pulldown   VO = 7 V   O.5   1.2   2.5   mA     IO(L)   Maximum current output for drive terminals, pulldown   VO = 7 V   O.5   1.2   2.5   mA     V(stb)   Short-to-battery/shorted-load/open-load detection voltage   VCOMPEN = L   1.1   1.25   1.4   V     Vhys(stb)   Short-to-battery hysteresis   40   100   150   mV     VD(open)   Open-load off-state detection voltage threshold   VCOMPEN = L   1.1   1.25   1.4   V     Vhys(open)   Open-load off-state detection current   30   60   80   μA     II(PU)   Input pullup current (CS)   VCC = 5 V, VIN = 0 V   10   μA     II(PU)   Input pulldown current   VCC = 5 V, VIN = 5 V   10   μA     Vhys   Input voltage hysteresis   VCC = 5 V   VIN = 5 V   10   0.6   0.85   1.1   V     VO(SH)   High-level serial output voltage   IO = 1 mA   0.8 VCC   V     VO(SL)   Low-level serial output voltage   IO = 1 mA   0.8 VCC   V     VO(CFLT)   Fault-interrupt output voltage   IO = 1 mA   0.1   0.4   V     VI(COMP)   Fault-external reference voltage   IO = 1 mA   0.1   0.5   V     VI(COMP)   Fault-external reference voltage   IO = 1 mA   0.25   3   V     VI(COMP)   Fault-external reference voltage   (TPIC44L01/L02 only)   VCOMPEN = H   0.25   3   V     VI(COMP)   Fault-external reference voltage   (TPIC44L01/L02 only)   VCOMPEN = H   1   3   V     VOC   Output clamp voltage   (TPIC44L01/L02 only)   VCOMPEN = H   1   3   V     VI(COMP)   Fault-external reference voltage   (TPIC44L01/L02 only)   VCOMPEN = H   1   3   V     VI(COMP)   Fault-external reference voltage   (TPIC44L01/L02 only)   VCOMPEN = H   1   1   3   V     VI(COMP)   VI(COMPEN = H   1   1   3   V   V     VI(COMPEN   Fault-external reference voltage   (TPIC44L01/L02 only)   VCOMPEN = H   1   1   1   1   1   1   1   1   1	.,	Gate drive voltage	8 V < V <sub>BAT</sub> < 24 V,	I <sub>O</sub> = 100 μA	7		13.5	V
O(H)   pullup	vG		5.5 V < V <sub>BAT</sub> < 8 V,	I <sub>O</sub> = 100 μA	5		7	V
O(L)   pulldown	I <sub>O(H)</sub>	•	V <sub>O</sub> = GND		0.5	1.2	2.5	mA
V(stb)         detection voltage         VCOMPEN = L         1.1         1.25         1.4         V           Vhys(stb)         Short-to-battery hysteresis         40         100         150         mV           VD(open)         Open-load off-state detection voltage threshold         VCOMPEN = L         1.1         1.25         1.4         V           Vhys(open)         Open-load off-state detection current         40         100         150         mV           Il(open)         Open-load off-state detection current         30         60         80         μA           Il(PU)         Input pullup current (CS)         V <sub>CC</sub> = 5 V,         V <sub>IN</sub> = 0 V         10         μA           Il(PD)         Input pulldown current         V <sub>CC</sub> = 5 V,         V <sub>IN</sub> = 5 V         10         μA           Vhys         Input voltage hysteresis         V <sub>CC</sub> = 5 V         0.6         0.85         1.1         V           VO(SH)         High-level serial output voltage         I <sub>O</sub> = 1 mA         0.8 V <sub>CC</sub> V           VO(SL)         Low-level serial output voltage         I <sub>O</sub> = 1 mA         0.1         0.4         V           IOZ(SD)         3-state current serial-data output         V <sub>CC</sub> = 0 V to 5.5 V         -10         1         10 <td>I<sub>O(L)</sub></td> <td>•</td> <td>V<sub>O</sub> = 7 V</td> <td></td> <td>0.5</td> <td>1.2</td> <td>2.5</td> <td>mA</td>	I <sub>O(L)</sub>	•	V <sub>O</sub> = 7 V		0.5	1.2	2.5	mA
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	V <sub>(stb)</sub>		VCOMPEN = L		1.1	1.25	1.4	V
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	V <sub>hys(stb)</sub>	Short-to-battery hysteresis			40	100	150	mV
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$		Open-load off-state detection voltage threshold	VCOMPEN = L		1.1	1.25	1.4	V
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	V <sub>hys</sub> (open)	Open-load hysteresis			40	100	150	mV
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	I <sub>I(open)</sub>	Open-load off-state detection current			30	60	80	μΑ
VhysInput voltage hysteresis $V_{CC} = 5 \text{ V}$ 0.60.851.1VVO(SH)High-level serial output voltageIO = 1 mA0.8 VCCVVO(SL)Low-level serial output voltageIO = 1 mA0.10.4VIOZ(SD)3-state current serial-data output $V_{CC} = 0 \text{ V to } 5.5 \text{ V}$ -10110 $\mu A$ VO(CFLT)Fault-interrupt output voltageIO = 1 mA0.10.5VVI(COMP)Fault-external reference voltage, (TPIC44L03 only)VCOMPEN = H0.253VVI(COMP)Fault-external reference voltage, (TPIC44L03 only)VCOMPEN = H13VVCOutput clamp voltage, (TPIC44L01/L02 only)dc < 1%, $t_W = 100 \mu s$ 475563V	I <sub>I(PU)</sub>	Input pullup current (CS)	$V_{CC} = 5 V$ ,	$V_{IN} = 0 V$		10		μΑ
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	I <sub>I(PD)</sub>	Input pulldown current	$V_{CC} = 5 V$ ,	V <sub>IN</sub> = 5 V		10		μΑ
VO(SL)Low-level serial output voltageIO = 1 mA0.10.4VIOZ(SD)3-state current serial-data output $V_{CC} = 0 \text{ V to } 5.5 \text{ V}$ -10110 $\mu A$ VO(CFLT)Fault-interrupt output voltageIO = 1 mA0.10.5VVI(COMP)Fault-external reference voltage, (TPIC44L01/L02 only)VCOMPEN = H0.253VVI(COMP)Fault-external reference voltage, (TPIC44L03 only)VCOMPEN = H13VVCOutput clamp voltage, (TPIC44L01/L02 only)dc < 1%,	$V_{hys}$	Input voltage hysteresis	$V_{CC} = 5 V$		0.6	0.85	1.1	V
IOZ(SD)3-state current serial-data output $V_{CC} = 0 \text{ V to } 5.5 \text{ V}$ -10110μA $V_{O(CFLT)}$ Fault-interrupt output voltage $I_{O} = 1 \text{ mA}$ 0.10.5V $V_{I(COMP)}$ Fault-external reference voltage, (TPIC44L01/L02 only) $V_{COMPEN} = H$ 0.253V $V_{I(COMP)}$ Fault-external reference voltage, (TPIC44L03 only) $V_{COMPEN} = H$ 13 $V_{COMPEN} = H$ $V_{COMPEN} = H$ 0.250.2563 $V_{COMPEN} = H$ $V_{COMPEN} = H$ 0.250.250.250.25 $V_{COMPEN} = H$ 0.250.250.250.250.25 $V_{COMPEN} = H$ 0.250.250.250.250.250.250.250.25 $V_{COMPEN} = H$ 0.25	V <sub>O</sub> (SH)	High-level serial output voltage	I <sub>O</sub> = 1 mA		0.8 V <sub>C</sub> C			V
VO(CFLT)     Fault-interrupt output voltage     I <sub>O</sub> = 1 mA     0.1     0.5     V       VI(COMP)     Fault-external reference voltage, (TPIC44L01/L02 only)     VCOMPEN = H     0.25     3     V       VI(COMP)     Fault-external reference voltage, (TPIC44L03 only)     VCOMPEN = H     1     3     V       VC     Output clamp voltage, (TPIC44L01/L02 only)     dc < 1%,	V <sub>O(SL)</sub>	Low-level serial output voltage	I <sub>O</sub> = 1 mA			0.1	0.4	V
VO(CFLT)Fault-interrupt output voltageIO = 1 mA0.10.5VVI(COMP)Fault-external reference voltage, (TPIC44L01/L02 only)VCOMPEN = H0.253VVI(COMP)Fault-external reference voltage, (TPIC44L03 only)VCOMPEN = H13VVCOutput clamp voltage, (TPIC44L01/L02 only)dc < 1%,		3-state current serial-data output	V <sub>CC</sub> = 0 V to 5.5 V		-10	1	10	μΑ
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$		Fault-interrupt output voltage	I <sub>O</sub> = 1 mA			0.1	0.5	V
VC Output clamp voltage, (TPIC44L01/L02 only) $dc < 1\%$ , $t_W = 100 \mu s$ 47 55 63 $V$		——————————————————————————————————————	VCOMPEN = H		0.25		3	V
	VI(COMP)		VCOMPEN = H		1		3	٧
$V_C$ Output clamp voltage, (TPIC44L03 only) dc < 1%, $t_W$ = 100 μs 47 53.5 60 V	VC	Output clamp voltage, (TPIC44L01/L02 only)	dc < 1%,	t <sub>W</sub> = 100 μs	47	55	63	V
	٧c	Output clamp voltage, (TPIC44L03 only)	dc < 1%,	t <sub>W</sub> = 100 μs	47	53.5	60	V



# switching characteristics, $V_{CC}$ = 5 V, $V_{bat}$ = 12 V, $T_{C}$ = 25°C

	PARAMETER	TEST COND	MIN	TYP	MAX	UNIT	
t(STBFM)	Short-to-battery/shorted-load/open-load fault mask time	See Figures 14 and 15			60		μs
t(STBDG)	Short-to-battery/shorted-load deglitch time	See Figure 14			8		μs
<sup>t</sup> PLH	Propagation turnon delay time, $\overline{\text{CS}}$ or IN0-IN3 to GATE0–GATE3	C <sub>(gate)</sub> = 400 pF,	See Figure 1		4		μs
<sup>t</sup> PHL	Propagation turnoff delay time, $\overline{\text{CS}}$ or IN0-IN3 to GATE0–GATE3	C <sub>(gate)</sub> = 400 pF,	See Figure 2		3.5		μs
tr(1)	Rise time GATE0-GATE3	C <sub>(gate)</sub> = 400 pF,	See Figure 3		3.5		μs
<sup>t</sup> f(1)	Fall time, GATE0-GATE3	C <sub>(gate)</sub> = 400 pF,	See Figure 4		3		μs
f(SCLK)	Serial clock frequency					10	MHz
trf(SB)	Refresh time, short-to-battery	TPIC46L01 only,	See Figure 14		10		ms
t <sub>W</sub>	Refresh pulse width, short-to-battery	TPIC46L01 only,	See Figure 14		68		μs
tsu(1)	Setup time, CS↓ to ↑SCLK	See Figure 5			10		ns
<sup>t</sup> pd(1)	Propagation delay time, CS↓ to SDO valid	$R_L$ = 10 kΩ, See Figure 6	C <sub>L</sub> = 200 pF,		40		ns
tpd(2)	Propagation delay time, SCLK↓ to SDO valid	See Figure 6			20		ns
tpd(3)	Propagation delay time, CS↑ to SDO 3-state	$R_L$ = 10 kΩ, See Figure 7	$C_L = 50 \text{ pF},$		2		μs
t <sub>r2</sub>	Rise time, SDO 3-state to SDO valid	$R_L = 10 \text{ k}\Omega \text{ to GND},$ $C_L = 200 \text{ pF},$	Over-battery fault, See Figure 8		30		ns
<sup>t</sup> f(2)	Fall time, SDO 3-state to SDO valid	$R_L = 10 \text{ k}\Omega \text{ to V}_{CC},$ $C_L = 200 \text{ pF},$	No faults, See Figure 9		20		ns
<sup>t</sup> r(3)	Rise time, FLT	$R_L$ = 10 kΩ, See Figure 10	C <sub>L</sub> = 50 pF,		1.2		μs
<sup>t</sup> f(3)	Fall time, FLT	$R_L$ = 10 kΩ, See Figure 11	C <sub>L</sub> = 50 pF,		15		ns



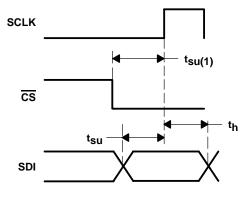


Figure 5

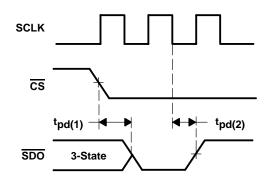


Figure 6

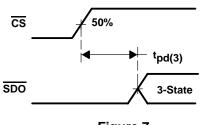


Figure 7

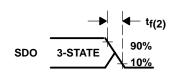


Figure 9

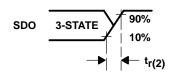


Figure 8

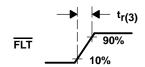


Figure 10

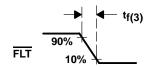


Figure 11

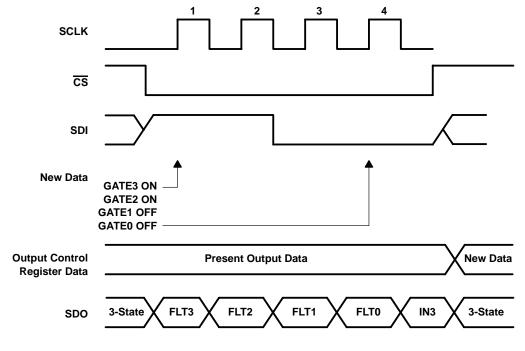
#### PRINCIPLES OF OPERATION

## serial data operation

The TPIC44L01, TPIC44L02, and TPIC44L03 offer serial input interface to the microcontroller to transfer control data to the predriver and fault data back to the controller. The serial input interface consists of:

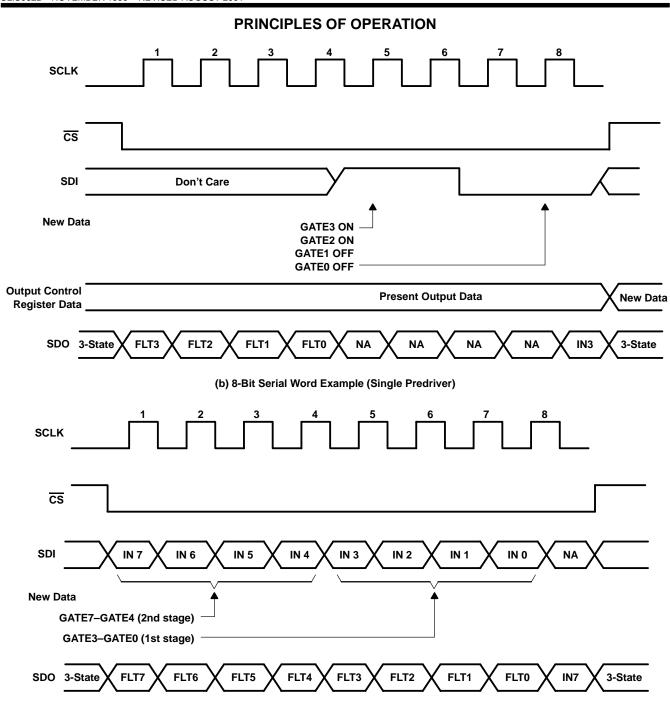
- SCLK Serial clock
- SDI Serial data input
- SDO Serial data output

Serial data is shifted into the least significant bit (LSB) of the SDI shift register on the rising edge of the first SCLK after  $\overline{CS}$  has transitioned from 1 to 0. Four clock cycles are required to shift the first bit from the LSB to the most significant bit (MSB) of the shift register. Four clock cycles must occur before  $\overline{CS}$  transitions high for proper control of the outputs. Less than four clock cycles result in fault data being latched into the output control buffer. Eight bits of data can be shifted into the device, but the first 4 bits shifted out are always the fault data and the last 4 bits shifted in are always the output control data. A low-to-high transition on  $\overline{CS}$  latches the contents of the serial shift register into the output control register. A logic 0 input to SDI turns the corresponding parallel output off and a logic 1 input turns the output on (see Figure 12).



(a) 4-Bit Serial Word Example

Figure 12



(c) 8-Bit Serial Word Example (Cascade: Two Predrivers)

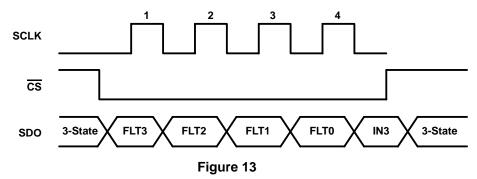
Figure 12 (continued)



#### PRINCIPLES OF OPERATION

# serial data operation (continued)

Data is shifted out of SDO on the falling edge of SCLK. The MSB of fault data is available after  $\overline{CS}$  is transitioned low. The remaining 3 bits of fault data are shifted out in the following three clock cycles. Fault data is latched into the serial register when  $\overline{CS}$  is transitioned low. A fault must be present on the high to low transition of  $\overline{CS}$  to be captured by the device. The  $\overline{CS}$  input must be transitioned to a high state after the last bit of serial data has been clocked into the device. The rising edge of  $\overline{CS}$  inhibits SDI, puts SDO into a high-impedance state, latches the 4 bits of serial data into the output control register, and clears and reenable the serial fault registers (see Figure 13). When a shorted-load condition occurs with the TPIC44L01 or TPIC44L03, then the controller must disable and reenable the channel to clear the fault register and  $\overline{FLT}$ . The TPIC44L02 automatically retries the output and the fault clears after the fault condition has been corrected.



## parallel input data operation

In addition to the serial interface, the TPIC44L01, TPIC44L02, and TPIC44L03 also provides a parallel interface to the microcontroller. The output turns on when either the parallel or the serial interface commands it to turn on. The parallel data terminals are real-time control inputs for the output drivers. SCLK and  $\overline{\text{CS}}$  are not required to transfer parallel input data to the output buffer. Fault data must be read over the serial data bus as described in the serial data operation section of this data sheet. The parallel input must be transitioned low and then high to clear and reenable a gate output after it has been disabled due to a shorted-load fault condition.

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#### PRINCIPLES OF OPERATION

## chipset performance under fault conditions

The TPIC44L01, TPIC44L02, TPIC44L03, and power FET arrays are designed for normal operation over a battery-voltage range of 8 V to 24 V with load-fault detection from 4.8 V to 34 V. The TPIC44L01, TPIC44L02, and TPIC44L03 offer onboard fault detection to handle a variety of faults that may occur within a system. The circuits primary function is to prevent damage to the load and the power FETs in the event that a fault occurs. Note that unused DRAIN0-DRAIN3 inputs must be connected to V<sub>BAT</sub> through a pullup resistor to prevent false reporting of open-load fault conditions. The circuitry detects the fault, shuts off the output to the FET, and reports the fault to the microcontroller. The primary faults under consideration are:

- 1. Shorted load
- 2. Open load
- 3. Over-battery voltage shutdown
- 4. Under-battery voltage shutdown (TPIC44L01 and TPIC44L02 only)

#### NOTE:

An undervoltage fault may be detected when  $V_{CC}$  and  $V_{BAT}$  are applied to the device. The controller should initialize the fault register after power up to clear any false fault reports.

#### shorted-load fault condition

The TPIC44L01, TPIC44L02, and TPIC44L03 monitor the drain voltage of each channel to detect shorted-load conditions. The onboard deglitch timer starts running when the gate output to the power FET transitions from the off state to the on state. The timer provides a 60- $\mu$ s deglitch time,  $t_{(STBFM)}$ , to allow the drain voltage to stabilize after the power FET has been turned on. The deglitch time is only enabled for the first 60  $\mu$ s after the FET has been turned on. After the deglitch delay time, the drain voltage is checked to verify that it is less than the fault reference voltage. When it is greater than the reference voltage for at least the short-to-battery deglitch time,  $t_{(STBDG)}$ , FLT flags the microcontroller that a fault condition exists and the gate output is automatically shut off (TPIC44L01 and TPIC44L03) until the error condition has been corrected.

An overheating condition on the FET occurs when the controller continually tries to reenable the output under shorted-load fault conditions. When a shorted-load fault is detected using the TPIC44L02, the gate output is transitioned into a low-duty cycle, PWM signal to to protect the FET from overheating. The PWM rate is defined as  $t_{(SB)}$  and the pulse width is defined as  $t_{w}$ . The gate output remains in this state until the fault has been corrected or until the controller disables the gate output.

The microcontroller can read the serial port on the predriver to isolate which channel reported the fault condition. Fault bits 0-3 distinguish faults for each of the output channels. When a shorted-load condition occurs with the TPIC44L01 or TPIC44L03, the controller must disable and reenable the channel to clear the fault register and FLT. The TPIC44L02 automatically retries the output and the fault clears after the fault condition has been corrected. Figure 14 illustrates operation after a gate output has been turned on. The gate to the power FET is turned on and the deglitch timer starts running. Under normal operation T1 turns on and the drain operates below the reference point set at U1. The output of U1 is low and a fault condition is not flagged.



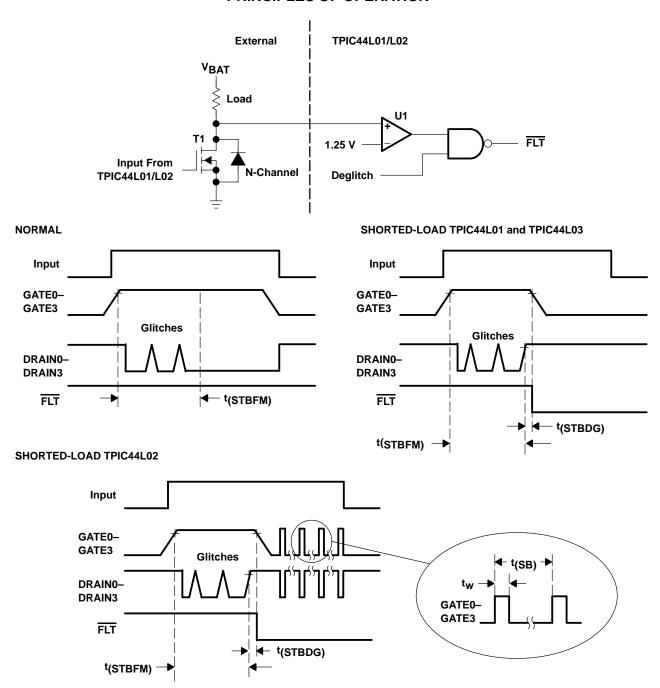


Figure 14

## open load

The TPIC44L01, TPIC44L02, and TPIC44L03 monitor the drain of each power FET for open circuit conditions that may exist. The 60-µA current source is provided to monitor open load fault conditions. Open-load faults are only detected when the power FET is turned off. When load impedance is open or substantially high, the 60-μA current source has adequate drive to pull the drain of T1 below the fault reference threshold on the detection circuit. Unused DRAIN0-DRAIN3 inputs must be connected to VBAT through a pullup resistor to prevent false reporting of open-load fault conditions. The onboard deglitch timer starts running when the TPIC44L01, TPIC44L02, and TPIC44L03 gate output to the power FET transitions to the off state. The timer provides a 60-μs deglitch time, t(STBFM) to allow the drain voltage to stabilize after the power FET has been turned off. The deglitch time is only enabled for the first 60 µs after the FET has been turned off. After the deglitch delay time, the drain is checked to verify that it is greater than the fault reference voltage. When it is less than the reference voltage, a fault is flagged to the microcontroller through FLT that an open-load fault condition exists. The microcontroller can then read the serial port on the TPIC44L01, TPIC44L02, and TPIC44L03 to isolate which channel reported the fault condition. Fault bits 0-3 distinguish faults for each of the output channels. Figure 15 illustrates the operation of the open-load detection circuit. This feature provides useful information to the microcontroller to isolate system failures and warn the operator that a problem exists. Examples of such applications would be a warning that a light bulb filament may be open, solenoid coils may be open, etc.

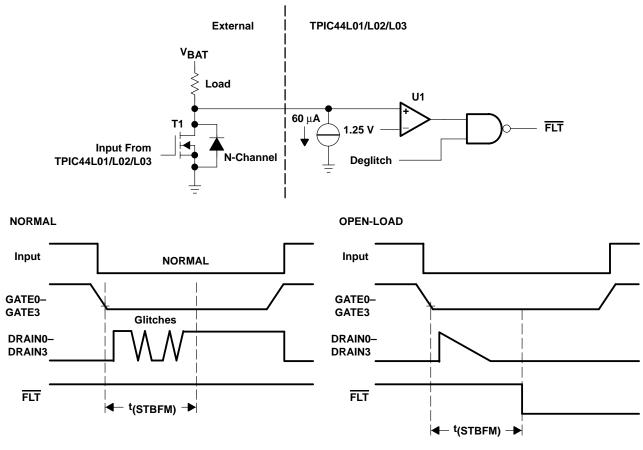


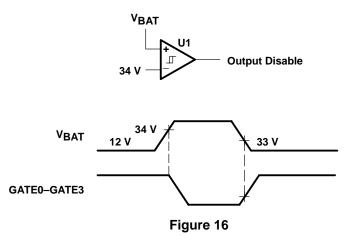
Figure 15



#### PRINCIPLES OF OPERATION

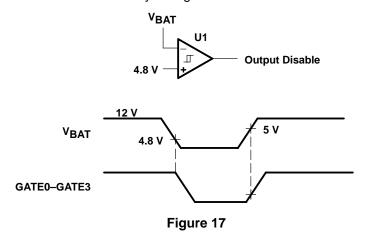
# over-battery-voltage shutdown

The TPIC44L01,TPIC44L02, and TPIC44L03 monitor the battery voltage to prevent the power FETs turning on in the event that the battery voltage is too high. This condition may occur due to voltage transients resulting from a loose battery connection. The TPIC44L01, TPIC44L02, and TPIC44L03 turns the power FET off when the battery voltage is above 34 V to prevent possible damage to the load and the FET. GATE(0–3) output goes back to normal operation after the overvoltage condition has been corrected. An over-battery voltage fault is flagged to the controller through  $\overline{\text{FLT}}$ . The over-battery voltage fault is not reported in the serial fault word. When an overvoltage condition occurs, the device reports the battery fault, but disables fault reporting for open and shorted-load conditions. Fault reporting for open and shorted-load conditions are reenabled after the battery fault condition has been corrected. When the fault condition is removed before the  $\overline{\text{CS}}$  signal transitions low, the fault condition is not captured in the serial fault register. The fault flag resets on a high-to-low transition of  $\overline{\text{CS}}$  provided no other faults are present in the device. Figure 16 illustrates the operation of the over-battery voltage detection circuit.



## under-battery-voltage shutdown (TPIC44L01 and TPIC44L02 only)

The TPIC44L01 and TPIC44L02 monitor the battery voltage to prevent the power FETs from being turned on in the event that the battery voltage is too low. When the battery voltage is below 4.8 V, then GATE0–GATE3 may not provide sufficient gate voltage to the power FETs to minimize the on-resistance that could result in a thermal stress on the FET. The output goes back to normal operation after the undervoltage condition has been corrected. An under-battery voltage fault is flagged to the controller through  $\overline{\text{FLT}}$ . The under-battery voltage fault is not reported in the serial fault word. When an under-battery voltage condition occurs, the device reports the battery fault but disables fault reporting for open- and shorted-load conditions. When the fault condition is removed before the  $\overline{\text{CS}}$  signal transitions low, the fault condition is not captured in the serial fault register. The fault flag resets on a high-to-low transition of  $\overline{\text{CS}}$  provided no other faults are present in the device. Figure 17 illustrates the operation of the under-battery voltage detection circuit.



#### PRINCIPLES OF OPERATION

## inductive voltage transients

A typical application for the predriver/power FET circuit is to switch inductive loads. When an inductive load is switched off, a large voltage spike can occur. These spikes can exceed the maximum V<sub>DS</sub> rating for the external FET and damage the device when the proper protection is not in place. The FET can be protected from these transients through a variety of methods using external components. The TPIC44L01, TPIC44L02, and TPIC44L03 offer that protection in the form of a Zener diode stack connected between the DRAIN input and GATE output (see Figure 18). Zener diode Z1 turns the FET on to dissipate the transient energy. GATE diode Z2 is provided to prevent the gate voltage from exceeding 13 V during normal operation and transient protection.

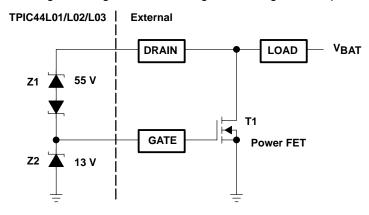


Figure 18

## external fault reference input

The TPIC44L01, TPIC44L02, and TPIC44L03 compare each channel drain voltage to a fault reference to detect shorted-load and open-load conditions. The user has the option of using the internally generated 1.25-V fault reference or providing an external reference voltage through VCOMP. The internal reference is selected by connecting VCOMPEN to GND and VCOMP is selected by connecting VCOMPEN to V<sub>CC</sub> (see Figure 19). Proper layout techniques should be used in the grounding network for the VCOMP circuit on the TPIC44L01, TPIC44L02, and TPIC44L03. The ground for the predriver and VCOMP network should be connected to a Kelvin ground if available; otherwise, they should make single-point contact back to the power ground of the FET array. Improper grounding techniques can result in inaccuracies in detecting faults.

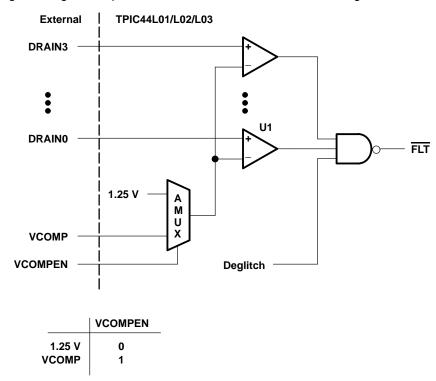


Figure 19

# **MECHANICAL DATA**

# DB (R-PDSO-G\*\*)

# PLASTIC SMALL-OUTLINE PACKAGE

#### 28 TERMINAL SHOWN 0,38 0,65 $\overline{\Phi}$ 0,15 M 0,22 28 15 0,15 NOM 5,60 8,20 5,00 7,40 **Gage Plane** 14 0,25 1,03 0,63 **Seating Plane** 0,10 2,00 MAX 0,05 MIN PINS \*\* 8 14 16 20 24 28 30 38 DIM A MAX 3,30 6,50 6,50 7,50 8,50 10,50 10,50 12,90 A MIN 2,70 5,90 5,90 6,90 7,90 9,90 9,90 12,30

NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.

D. Falls within JEDEC MO-150

4040065/C 10/95

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